





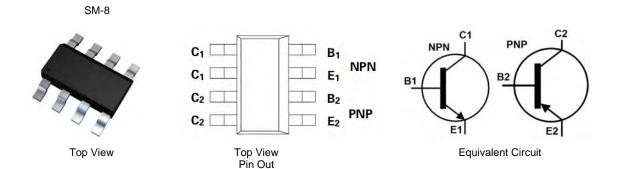
### COMPLEMENTARY MEDIUM POWER HIGH GAIN TRANSISTOR IN SM-8 PACKAGE

### **Features**

- NPN Transistor
  - BV<sub>CEO</sub> > 45
  - V<sub>CE(sat)</sub> < 100mV @ I<sub>C</sub>= 100mA
  - Continuous Current I<sub>C</sub> = 2A
- PNP Transistor
  - BV<sub>CEO</sub> > -40V
  - V<sub>CE(sat)</sub> < 250mV @ I<sub>C</sub>= -500mA
  - Continuous Current I<sub>C</sub> = -2A
- Lead-Free Finish; RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

### **Mechanical Data**

- Case: SM-8 (8 LEAD SOT223)
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Matte Tin Finish @3
- Weight: 0.117 grams (approximate)



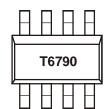
## **Ordering Information** (Note 4)

Part Number	Marking	Reel size (inches)	Tape width (mm)	Quantity per reel
ZDT6790TA	T6790	7	12	1,000
ZDT6790TC	T6790	13	12	4,000

Notes:

- 1. EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant. All applicable RoHS exemptions applied.
- 2. See http://www.diodes.com for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at http://www.diodes.com

## **Marking Information**



T6790 = Product Type Marking Code





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# **Maximum Ratings** (@ $T_A = +25^{\circ}C$ , unless otherwise specified.)

Characteristic	Symbol	Symbol NPN		Unit	
Collector-Base Voltage	V <sub>CBO</sub>	45	-50	V	
Collector-Emitter Voltage	V <sub>CEO</sub>	45	-40	V	
Emitter-Base Voltage	V <sub>EBO</sub>	6	-6	V	
Continuous Collector Current	Ic	2	-2	Α	
Peak Pulse Current (Note 5)	Ісм	6	-6	А	

# Thermal Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

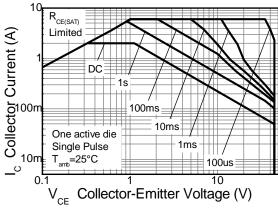
Characteristic	Symbol	Value	Unit		
Collector Power Dissipation	(Note 5)	D-	2.25	W	
Collector Fower Dissipation	(Note 6)	P <sub>D</sub>	2.75	VV	
Thermal Resistance, Junction to Ambient	(Note 5)	0	55.60	°C/W	
Thermal Resistance, Junction to Ambient	(Note 6)	$R_{\theta JA}$	45.50	-C/VV	
Thermal Resistance, Junction to Leads (Note 7)		$R_{ heta JL}$	30.68	°C/W	
Operating and Storage Temperature Range		$T_{J,}T_{STG}$	-55 to +150	°C	

Notes:

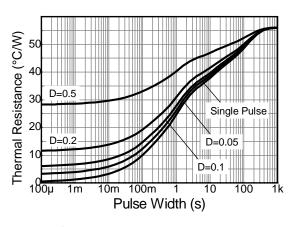
- 5. For the device with any single die active, mounted on 25mm x 25mm FR4 PCB with high coverage of single sided 2oz copper, in still air conditions . 6. For the device with both die active, mounted on 25mm x 25mm FR4 PCB with high coverage of single sided 2oz copper, in still air conditions.
- 7. Thermal resistance from junction to solder-point (at the end of the collector lead).



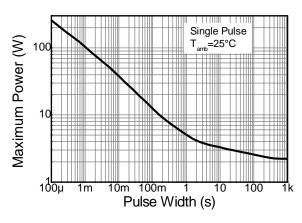
### **Thermal Characteristics**



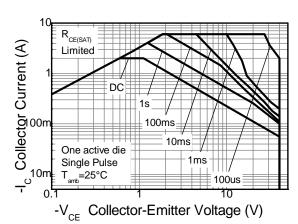
**NPN Safe Operating Area** 



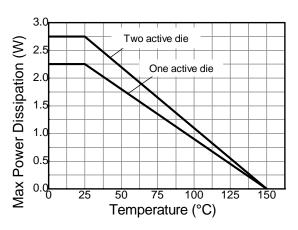
**Transient Thermal Impedance** 



**Pulse Power Dissipation** 



PNP Safe Operating Area



**Derating Curve** 





# NPN - Electrical Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

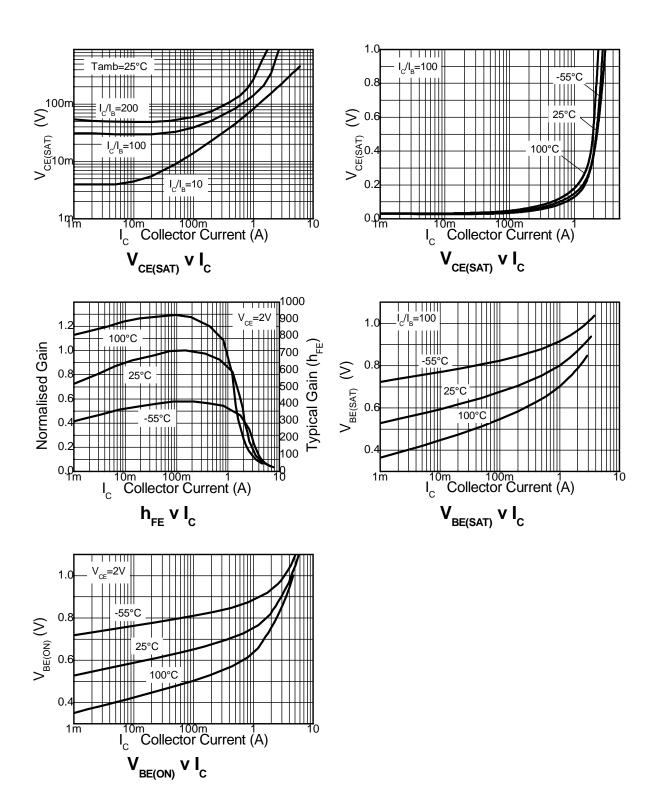
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
Collector-Base Breakdown Voltage	$BV_CBO$	45		I	V	$I_C = 100\mu A$
Collector-Emitter Breakdown Voltage (Note 8)	$BV_CEO$	45	1	1	V	$I_C = 10mA$
Emitter-Base Breakdown Voltage	$BV_{EBO}$	6	-	_	V	$I_E = 100\mu A$
Collector Cutoff Current	$I_{CBO}$	_	1	100	nA	$V_{CB} = 35V$
Emitter Cutoff Current	I <sub>EBO</sub>	_	ı	100	nA	$V_{EB} = 5V$
DC Current Transfer Static Ratio (Note 8)	h <sub>EE</sub>	500 400		1 1	_	$I_C = 100 \text{mA}, V_{CE} = 2V$ $I_C = 1A, V_{CE} = 2V$
( ,	-46	150	_	_		$I_C = 2A$ , $V_{CE} = 2V$
Collector-Emitter Saturation Voltage (Note 8)	V <sub>CE(sat)</sub>	_	_	100 500	mV	$I_C = 100 \text{mA}, I_B = 0.5 \text{mA}$ $I_C = 1 \text{A}, I_B = 5 \text{mA}$
Base-Emitter Saturation Voltage (Note 8)	V <sub>BE(sat)</sub>	_	_	900	mV	I <sub>C</sub> = 1A, I <sub>B</sub> = 10mA
Base-Emitter Turn-on Voltage (Note 8)	$V_{BE(on)}$	_	_	900	mV	$I_C = 1A$ , $V_{CE} = 2V$
Transitional Frequency (Note 8)	f <sub>T</sub>	150	1	1	MHz	$I_C = 50$ mA, $V_{CE} = 5$ V, $f = 50$ MHz
Input Capacitance	$C_{ibo}$	_	200	_	pF	$V_{EB} = 0.5V$ , $f = 1MHz$
Output Capacitance	$C_obo$	_	16	_	pF	$V_{CB} = 10V, f = 1MHz$
Switching Time	t <sub>on</sub>		33		ns	$V_{CC} = 10V, I_{C} = 500mA,$
Ownering Time	t <sub>off</sub>		1300		ns	$I_{B1} = 50 \text{mA}, I_{B2} = 50 \text{mA}$

Note:

8. Measured under pulsed conditions. Pulse width =  $300\mu$ s. Duty cycle  $\leq 2\%$ .



## **NPN - Typical Electrical Characteristics**







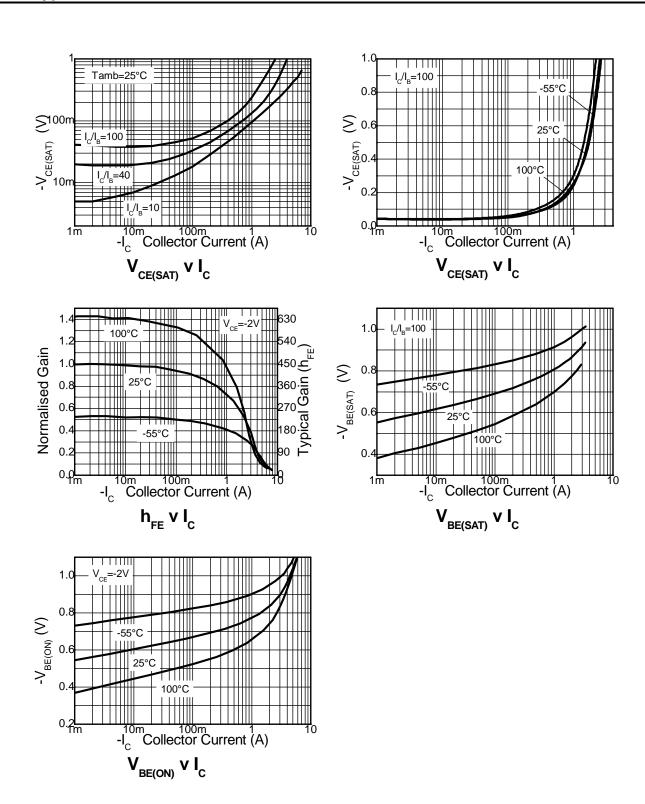
# PNP - Electrical Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
Collector-Base Breakdown Voltage	$BV_{CBO}$	-50		_	V	$I_{C} = -100 \mu A$
Collector-Emitter Breakdown Voltage (Notes 8)	BV <sub>CEO</sub>	-40	ı	_	V	I <sub>C</sub> = -10mA
Emitter-Base Breakdown Voltage	$BV_{EBO}$	-6		_	V	I <sub>E</sub> = -100μA
Collector Cutoff Current	I <sub>CBO</sub>	_		-100	nA	V <sub>CB</sub> = -30V
Emitter Cutoff Current	I <sub>EBO</sub>	_		-100	nA	V <sub>EB</sub> = -5V
DC Current Transfer Static Ratio (Notes 8)	h <sub>FE</sub>	300 250 200 150		800 — — —	_	$\begin{split} I_{C} &= -10 \text{mA}, \ V_{CE} = -2 \text{V} \\ I_{C} &= -500 \text{mA}, \ V_{CE} = -2 \text{V} \\ I_{C} &= -1 \text{A}, \ V_{CE} = -2 \text{V} \\ I_{C} &= -2 \text{A}, \ V_{CE} = -2 \text{V} \end{split}$
Collector-Emitter Saturation Voltage (Notes 8)	V <sub>CE(sat)</sub>	_	1 1 1	-250 -450 -750	mV	$I_C = -500$ mA, $I_B = -5$ mA $I_C = -1$ A, $I_B = -10$ mA $I_C = -2$ A, $I_B = -50$ mA
Base-Emitter Saturation Voltage (Notes 8)	$V_{BE(sat)}$	_		-1000	mV	$I_C = -1A$ , $I_B = -10mA$
Base-Emitter Turn-on Voltage (Notes 8)	$V_{BE(on)}$	_	-750	_	mV	$I_C = -1A$ , $V_{CE} = -2V$
Transitional Frequency (Notes 8)	$f_T$	100	1	_	MHz	$I_C = -50 \text{mA}, V_{CE} = -5 \text{V},$ f = 50MHz
Input Capacitance	C <sub>ibo</sub>	_	225	_	pF	$V_{EB} = -0.5V, f = 1MHz,$
Output Capacitance	$C_obo$	_	24	_	pF	$V_{CB} = -10V$ , $f = 1MHz$ ,
Switching Time	t <sub>on</sub>		35		ns	$V_{CC} = -10V, I_{C} = -500mA,$
Switching Time	t <sub>off</sub>		600		ns	$I_{B1} = -50 \text{mA}, I_{B2} = -50 \text{mA}$

Notes: 8. Measured under pulsed conditions. Pulse width =  $300\mu$ s. Duty cycle  $\leq 2\%$ .

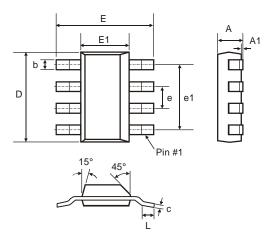


## **PNP – Typical Electrical Characteristics**



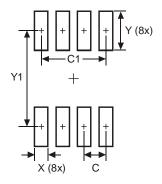


# **Package Outline Dimensions**



SM-8					
Dim	Min	Max	Тур		
Α	_	1.7	_		
A1	0.02	0.1	-		
b	_	0.7	-		
С	0.24	0.32	-		
D	6.3	6.7	-		
е	_	_	1.53		
e1	_	_	4.59		
E	6.7	7.3	-		
E1	3.3	3.7	-		
L	0.9	-	-		
All Dimensions in mm					

## **Suggested Pad Layout**



Dimensions	Value (in mm)		
С	1.52		
C1	4.6		
Х	0.95		
Y	2.80		
Y1	6.80		





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